SiC Schottky Barrier Diode

Datasheet

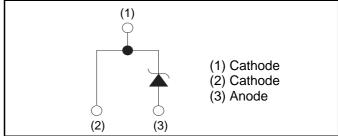
V_R	1200V
I _F	20A
Q_{C}	65nC

●Outline TO-220AC (1) (2) (3)

Features

- 1) Shorter recovery time
- 2) Reduced temperature dependence
- 3) High-speed switching possible

●Inner circuit



Applications

- PFC Boost Topology
- Secondary Side Rectification
- Data Center
- PV Power Conditioners

Packaging specifications

	ging opcomouncing	
	Packaging	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	50
	Packing code	С
	Marking	SCS220KG

● Absolute maximum ratings (T_i = 25°C)

Parameter		Symbol	Value	Unit
Reverse voltage (repetitive peak)		V_{RM}	1200	V
Reverse voltage (D	C)	V_R	1200	V
Continuous forward	current (T _c = 133°C)	I _F	20	А
Surge non-			79	А
repetitive forward	PW=10ms sinusoidal, T _j =150°C	I_{FSM}	59	А
current	PW=10μs square, T _j =25°C		310	А
Repetitive peak forward current		I _{FRM}	83 ^{*1}	А
$i^{2}t \text{ value}$ $PW=10\text{ms}, T_{j}=25^{\circ}\text{C}$ $PW=10\text{ms}, T_{j}=150^{\circ}\text{C}$		$\int i^2 dt$	31	A ² s
		J i⁻dt	17	A ² s
Total power dissipation		P_D	210 ^{*2}	W
Junction temperature		T _j	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

^{*1} T_c=100°C, T_i=150°C, Duty cycle=10% *2 T_c=25°C

●Electrical characteristics (T_j = 25°C)

Parameter	Symbol	Conditions	Values			Linit
			Min.	Тур.	Max.	Unit
DC blocking voltage	V_{DC}	I _R =0.4mA	1200	-	-	V
Forward voltage	V _F	I _F =20A,T _j =25°C	-	1.4	1.6	V
		I _F =20A,T _j =150°C	-	1.8	-	V
		I _F =20A,T _j =175°C	-	1.9	-	V
Reverse current	I _R	V _R =1200V,T _j =25°C	-	20	400	μΑ
		V _R =1200V,T _j =150°C	-	160	-	μΑ
		V _R =1200V,T _j =175°C	-	260	-	μΑ
Total capacitance	С	V _R =1V,f=1MHz	-	1050	-	pF
		V _R =800V,f=1MHz	-	85	-	pF
Total capacitive charge	Q _C	V _R =800V,di/dt=500A/μs	-	65	-	nC
Switching time	t _C	V _R =800V,di/dt=500A/μs	-	18	-	ns

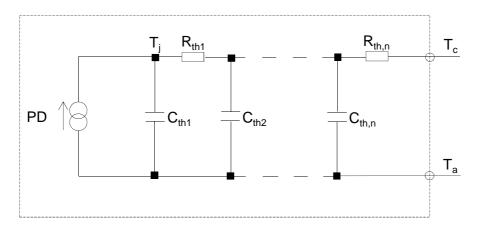
●Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	UIIIL
Thermal resistance	$R_{\text{th(j-c)}}$	-	-	0.62	0.71	°C/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.59E-01	
R _{th2}	2.74E-01	K/W
R _{th3}	1.87E-01	

Symbol	Value	Unit
C_{th1}	5.03E-03	
C_{th2}	7.27E-03	Ws/K
C_{th3}	1.39E-01	



•Electrical characteristic curves

Fig.1 V_F - I_F Characteristics

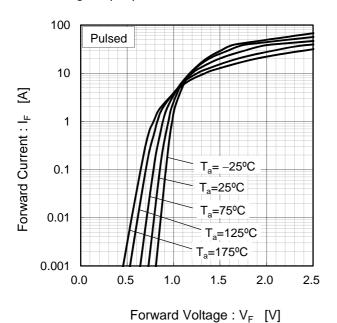
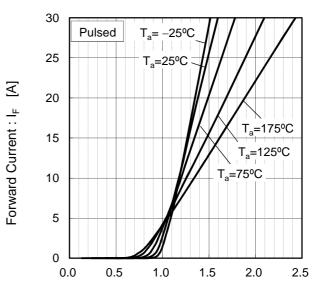


Fig.2 V_F - I_F Characteristics



Forward Voltage : V_F [V]

Fig.3 V_R - I_R Characteristics

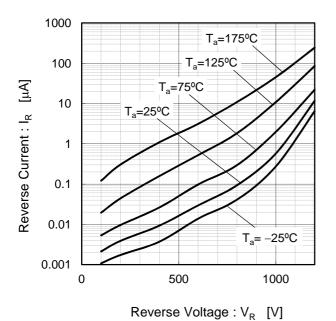
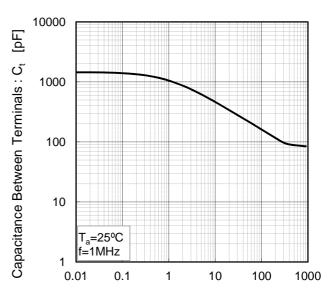


Fig.4 V_R - C_t Characteristics

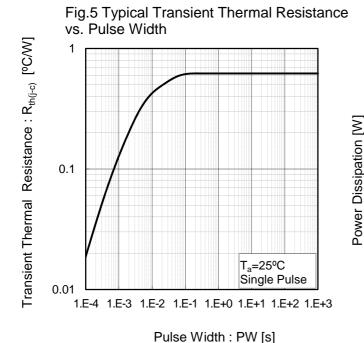


Reverse Voltage : V_R [V]

175

150

Electrical characteristic curves



250 200 150 100

Fig.6 Power Dissipation

50

25

50

75

Case Temperature : T_c [°C]

125

100

Fig.7*3 Maximum peak forward current derating curve I_P - T_c 200 Peak Forward Current: Ip [A] 150 Duty=0.1 100 Duty=0.2

Case Temperature : T_c [°C] *3 Based on max Vf, max R_{th(j-c)} Valid for switching of above 10kHz, excluding D.C. curve.

100

125

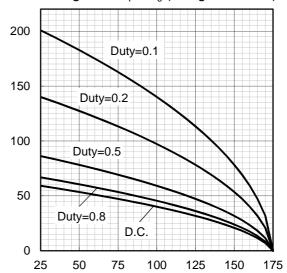
150

175

D.C

75

Fig.8*4 Typical peak forward current derating curve I_P - T_c (Not guaranteed)



Case Temperature : T_c [°C] *4 Based on typ Vf, typ $R_{th(j-c)}$ Typical value, not guaranteed Valid for switching of above 10kHz, excluding D.C. curve

Duty=0.5

Duty=0.8

50

50

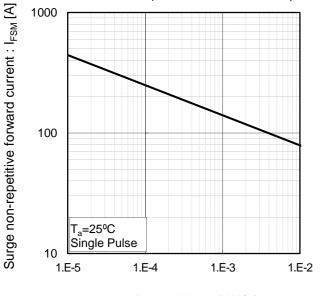
0

25

Peak Forward Current : IP [A]

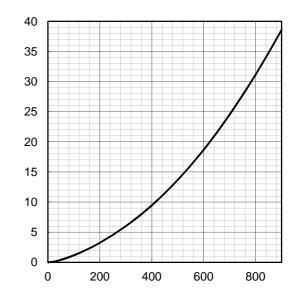
•Electrical characteristic curves

Fig.9 Surge non-repetitive forward current vs. Pulse width (Sinusoidal waveform)



Pulse Width: PW [s]

Fig.10 Typical capacitance store energy

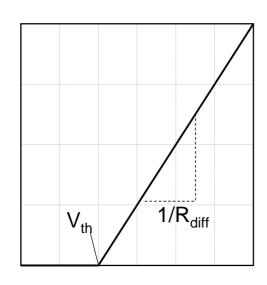


Capacitance stored energy : $\mathsf{E}_\mathsf{C}[\mu J]$

Reverse Voltage: V_R [V]

•Symplified forward characteristic model

Fig.11 Equivalent forward current curve



Forward Voltage: V_F

$$V_F = V_{th} + R_{diff} I_F$$

$$V_{th} (T_j) = a_0 + a_1 T_j$$

 $R_{diff} (T_j) = b_0 + b_1 T_j + b_2 T_j^2$

Symbol	Typical Value	Unit
a ₀	9.93E-01	V
a ₁	-1.27E-03	V/°C
b ₀	1.83E-02	Ω
b ₁	1.03E-04	Ω/°C
b ₂	6.65E-07	$\Omega/^{\circ}C^{2}$

 T_i in ${}^{\circ}C$; -55 ${}^{\circ}C$ < T_i < ${}^{\circ}C$; I_F < 40 A

Forward Current: IF

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